

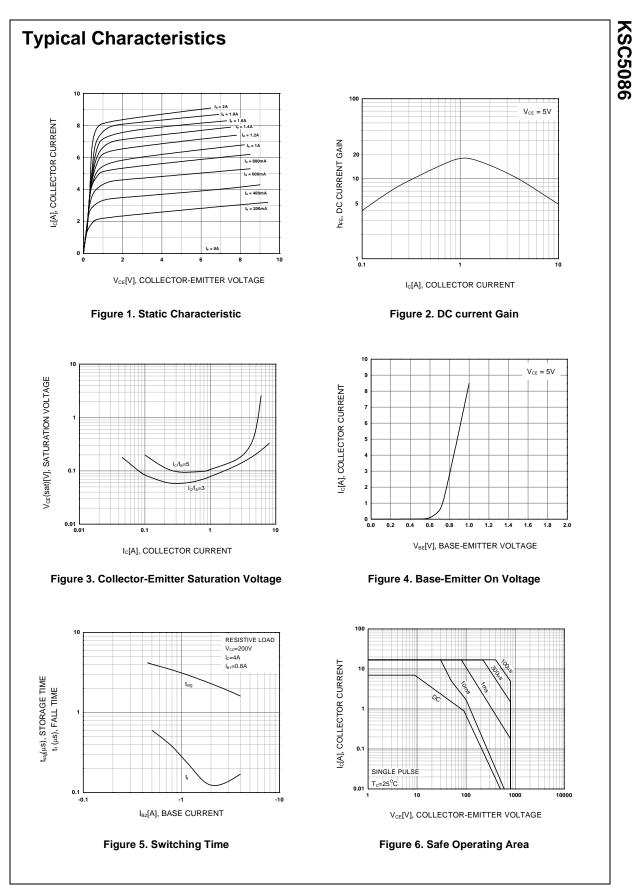
NPN Triple Diffused Planar Silicon Transistor

A	bsolut	e N	laximum	Ratir	ngs	T _C =25°C	unless otherwise noted	
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Symbol	Parameter	Value	
V _{CBO}	Collector-Base Voltage	1500	V
V _{CEO}	Collector-Emitter Voltage	800	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current (DC)	7	А
I _{CP}	Collector Current (Pulse)	16	А
P _C	Collector Dissipation (T _C =25°C)	50	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

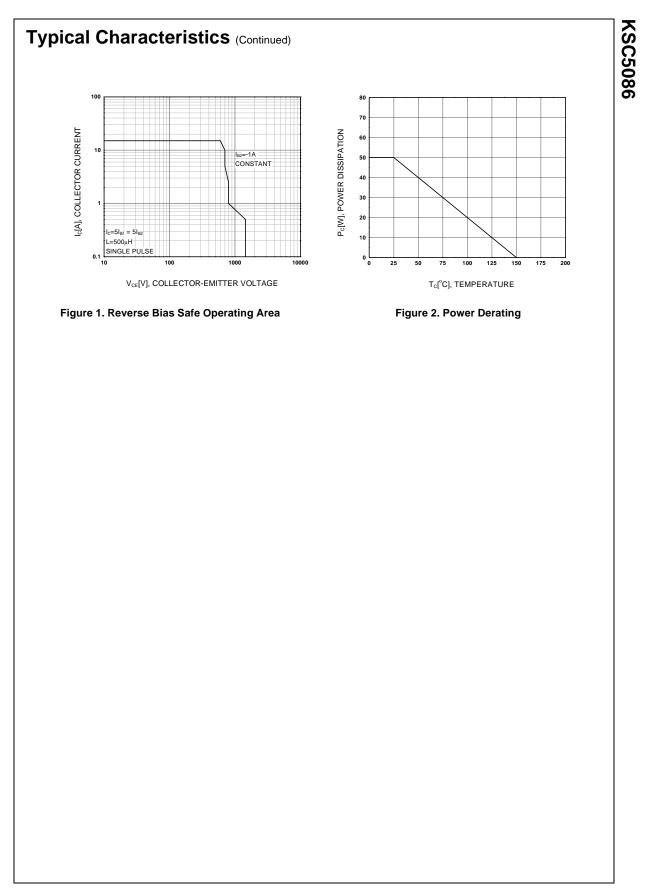
Electrical Characteristics T_C=25°C unless otherwise noted

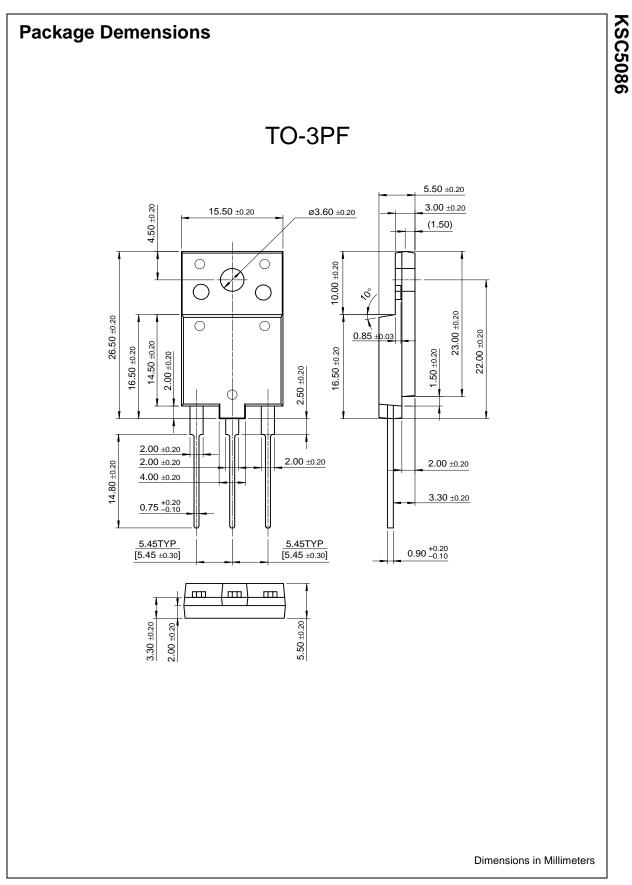
Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
I _{CES}	Collector Cut-off Current (V _{BE} =0)	V _{CE} = 1400V, R _{BE} = 0			1	mA
I _{CBO}	Collector Cu-toff Current	V _{CB} =800V, I _E =0			10	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 4V, I_{C} = 0$	40		200	mA
V _{EBO}	Base-Emitter Breakdown Voltage	I _E = 250mA, I _C = 0	6			V
h _{FE}	DC Current Gain	V _{CE} = 5V, I _C = 1.0A	8			
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = 5A, I _B = 1.2A			5	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = 5A, I _B = 1.2A			1.5	V
V _F	Damper Diode Turn On Voltage	I _F = 6A			2	V
t _F	Fall Time	$V_{CC} = 200V, I_C = 4A$ $I_{B1} = 0.8A, I_{B2} = -1.6A$ $R_L = 50\Omega$			0.2	μs



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